IRFP140

Vishay Siliconix



TO-247AC

PRODUCT SUMMARY

V_{DS} (V)

R_{DS(on)} (Ω)

Q_{qs} (nC)

Q_{gd} (nC)

Q_a (max.) (nC)

Configuration

Power MOSFET

S

N-Channel MOSFET

0.077

100

72

11

32

Single

 $V_{GS} = 10 V$

FEATURES

- Dynamic dV/dt rating
- · Repetitive avalanche rated
- · Isolated central mounting hole
- 175 °C operating temperature
- Fast switching
- · Ease of paralleling
- Simple drive requirements
- Material categorization: for definitions of compliance please see <u>www.vishav.com/doc?99912</u>

Note

* This datasheet provides information about parts that are RoHS-compliant and / or parts that are non RoHS-compliant. For example, parts with lead (Pb) terminations are not RoHS-compliant. Please see the information / tables in this datasheet for details

DESCRIPTION

Third generation Power MOSFETs from Vishay provide the designer with the best combination of fast switching, ruggedized device design, low on-resistance and cost-effectiveness.

The TO-247AC package is preferred for commercial-industrial applications where higher power levels preclude the use of TO-220AB devices. The TO-247AC is similar but superior to the earlier TO-218 package because of its isolated mounting hole. It also provides greater creepage distance between pins to meet the requirements of most safety specifications.

ORDERING INFORMATION	
Package	TO-247AC
Lead (Pb)-free	IRFP140PbF

ABSOLUTE MAXIMUM RATINGS (T _C	= 25 °C, unless otherwis	se noted)		
PARAMETER		SYMBOL	LIMIT	UNIT
Drain-source voltage		V _{DS}	100	V
Gate-source voltage		V _{GS}	± 20	V
Continuous drain current	V_{GS} at 10 V $T_C = 25 \degree C$ $T_C = 100 \degree C$	L_	31	
Continuous drain current	ID	22	А	
Pulsed drain current ^a		I _{DM}	120	
Linear derating factor		1.2	W/°C	
Single pulse avalanche energy ^b		E _{AS}	100	mJ
Repetitive avalanche current ^a		I _{AR}	31	А
Repetitive avalanche energy ^a		E _{AR}	18	mJ
Maximum power dissipation	T _C = 25 °C	PD	180	W
Peak Diode Recovery dV/dt c		dV/dt	5.5	V/ns
Operating junction and storage temperature range		T _J , T _{stg}	-55 to +175	°C
Soldering recommendations (peak temperature)	for 10 s		300 ^d	
Mounting torquo	6-32 or M3 screw		10	lbf ∙ in
Mounting torque	0-32 OF WIS SCIEW		1.1	N · m

Notes

a. Repetitive rating; pulse width limited by maximum junction temperature (see fig. 11)

b. V_{DD} = 25 V, starting T_J = 25 °C, L = 156 µH, R_g = 25 Ω , I_{AS} = 31 A (see fig. 12)

c. $I_{SD} \le 28$ A, dl/dt ≤ 170 A/µs, $V_{DD} \le V_{DS}$, $T_J \le 175$ °C

d. 1.6 mm from case

S22-0045-Rev. C, 24-Jan-2022



THERMAL RESISTANCE RAT	INGS			
PARAMETER	SYMBOL	TYP.	MAX.	UNIT
Maximum junction-to-ambient	R _{thJA}	-	40	
Case-to-sink, flat, greased surface	R _{thCS}	0.24	-	°C/W
Maximum junction-to-case (drain)	R _{thJC}	-	0.83	

SPECIFICATIONS ($T_J = 25 \text{ °C}$, u	Inless otherw	rise noted)					
PARAMETER	SYMBOL	TEST	CONDITIONS	MIN.	TYP.	MAX.	UNIT
Static	•			•		•	•
Drain-source breakdown voltage	V _{DS}	$V_{GS} = 0 V, I_D = 2$	50 µA	100	-	-	V
V _{DS} temperature coefficient	$\Delta V_{DS}/T_{J}$	Reference to 25	°C, I _D = 1 mA	-	0.13	-	V/°C
Gate-source threshold voltage	V _{GS(th)}	$V_{DS} = V_{GS}, I_D = 2$	250 μΑ	2.0	-	4.0	V
Gate-source leakage	I _{GSS}	$V_{GS} = \pm 20 V$		-	-	± 100	nA
Zere gete veltege drein eurrent		$V_{DS} = 100 \text{ V}, \text{ V}_{GS}$	_S = 0 V	-	-	25	
Zero gate voltage drain current	IDSS	$V_{DS} = 80 \text{ V}, \text{ V}_{GS}$	= 0 V, T _J = 150 °C	-	-	250	μA
Drain-source on-state resistance	R _{DS(on)}	V _{GS} = 10 V	I _D = 19 A ^b	-	-	0.077	Ω
Forward transconductance	9 _{fs}	$V_{DS} = 50 \text{ V}, \text{ I}_{D} =$	19 A ^b	9.8	-	-	S
Dynamic							
Input capacitance	C _{iss}	V _{GS} = 0 V,		-	1700	-	
Output capacitance	C _{oss}	$V_{DS} = 25 V,$		-	550	-	pF
Reverse transfer capacitance	C _{rss}	f = 1.0 MHz, see	e fig. 5	-	110	-	
Total gate charge	Qg			-	-	72	
Gate-source charge	Q _{gs}	V _{GS} = 10 V	$I_D = 17 \text{ A}, V_{DS} = 80 \text{ V}$ see fig. 6 and 13 ^b	-	-	11	nC
Gate-drain charge	Q _{gd}		obo ng. o unu ro	-	-	32	
Turn-on delay time	t _{d(on)}			-	11	-	
Rise time	t _r	$V_{DD} = 50 \text{ V}, \text{ I}_{D} =$		-	44	-	
Turn-off delay time	t _{d(off)}	$R_{g} = 9.1 \Omega, R_{D} =$	2.9Ω , see fig. 10 ^b	-	53	-	ns
Fall time	t _f			-	43	-	
Internal drain inductance	L _D	Between lead,	۵ لر	-	5.0	-	
Internal source inductance	L _S	6 mm (0.25") fro package and ce die contact		-	13	-	nH
Drain-Source Body Diode Characteristics	•			•		•	•
Continuous source-drain diode current	I _S	MOSFET symbo		-	-	31	
Pulsed diode forward current ^a	I _{SM}	showing the integral reverse p - n junction die	ode	-	-	120	A
Body diode voltage	V _{SD}	T _J = 25 °C, I _S = 3	31 A, V _{GS} = 0 V ^b	-	-	2.5	V
Body diode reverse recovery time	t _{rr}			-	180	360	ns
Body diode reverse recovery charge	Q _{rr}	$I_{\rm J} = 25$ °C, $I_{\rm F} = -$	17 A, dl/dt = 100 A/µs ^b	-	1.3	2.8	μC
Forward turn-on time	t _{on}	Intrinsic turn-on	time is neglegible (turn-o	n is domir	nated by I	_s and Ln)

Notes

a. Repetitive rating; pulse width limited by maximum junction temperature (see fig. 11)

b. Pulse width \leq 300 µs; duty cycle \leq 2 %



TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)

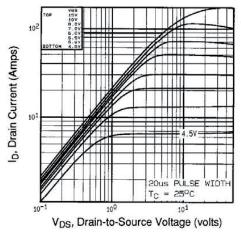


Fig. 1 - Typical Output Characteristics, T_C = 25 °C

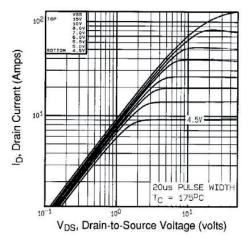


Fig. 2 - Typical Output Characteristics, $T_C = 175$ °C

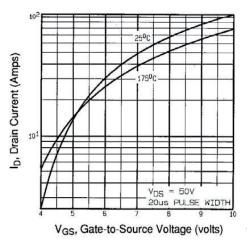


Fig. 3 - Typical Transfer Characteristics

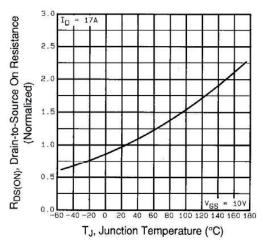


Fig. 4 - Normalized On-Resistance vs. Temperature

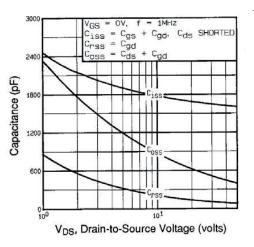


Fig. 5 - Typical Capacitance vs. Drain-to-Source Voltage

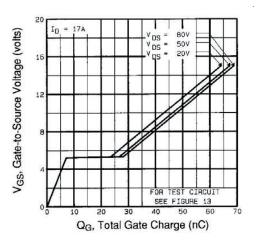


Fig. 6 - Typical Gate Charge vs. Gate-to-Source Voltage

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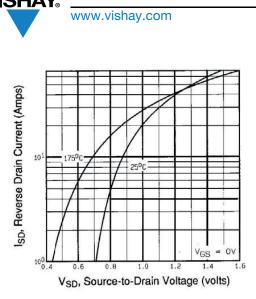


Fig. 7 - Typical Source-Drain Diode Forward Voltage

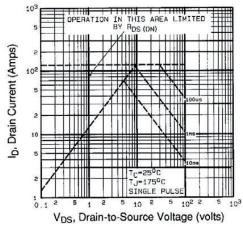


Fig. 8 - Maximum Safe Operating Area

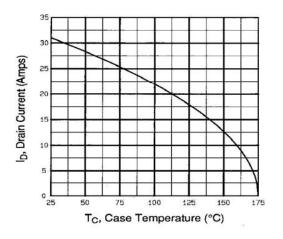


Fig. 9 - Maximum Drain Current vs. Case Temperature

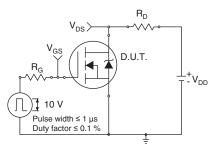


Fig. 10a - Switching Time Test Circuit

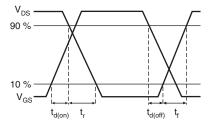


Fig. 10b - Switching Time Waveforms

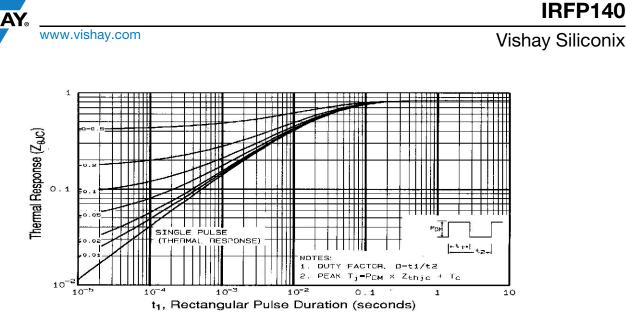


Fig. 11 - Maximum Effective Transient Thermal Impedance, Junction-to-Case

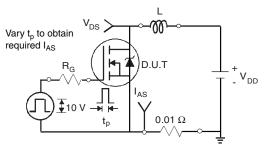


Fig. 12a - Unclamped Inductive Test Circuit

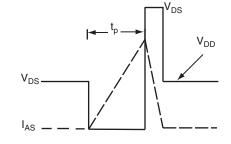


Fig. 12b - Unclamped Inductive Waveforms

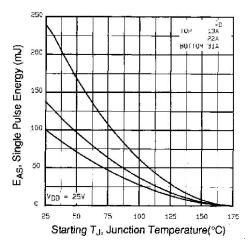


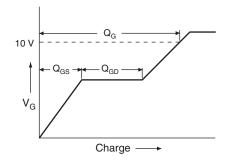
Fig. 12c - Maximum Avalanche Energy vs. Drain Current

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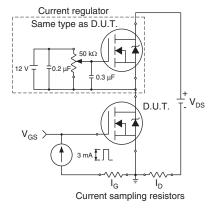


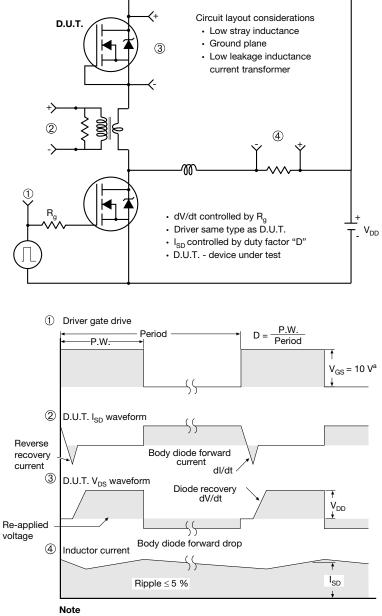
Fig. 13a - Basic Gate Charge Waveform

Fig. 13b - Gate Charge Test Circuit





Peak Diode Recovery dV/dt Test Circuit



a. V_{GS} = 5 V for logic level devices

Fig. 14 - For N-Channel

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TO-247AC (High Voltage)

VERSION 1: FACILITY CODE = 9





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	М	ILLIMETERS		
DIM.	MIN.	NOM.	MAX.	NOTES
А	4.83	5.02	5.21	
A1	2.29	2.41	2.55	
A2	1.17	1.27	1.37	
b	1.12	1.20	1.33	
b1	1.12	1.20	1.28	
b2	1.91	2.00	2.39	6
b3	1.91	2.00	2.34	
b4	2.87	3.00	3.22	6, 8
b5	2.87	3.00	3.18	
С	0.40	0.50	0.60	6
c1	0.40	0.50	0.56	
D	20.40	20.55	20.70	4

		MILLIMETERS	S	
DIM.	MIN.	NOM.	MAX.	NOTES
D1	16.46	16.76	17.06	5
D2	0.56	0.66	0.76	
E	15.50	15.70	15.87	4
E1	13.46	14.02	14.16	5
E2	4.52	4.91	5.49	3
е		5.46 BSC		
L	14.90	15.15	15.40	
L1	3.96	4.06	4.16	6
ØР	3.56	3.61	3.65	7
Ø P1	7.19 ref.			
Q	5.31	5.50	5.69	
S		5.51 BSC		

Notes

- ⁽¹⁾ Package reference: JEDEC[®] TO247, variation AC
- (2) All dimensions are in mm
- ⁽³⁾ Slot required, notch may be rounded
- ⁽⁴⁾ Dimension D and E do not include mold flash. Mold flash shall not exceed 0.127 mm per side. These dimensions are measured at the outermost extremes of the plastic body
- ⁽⁵⁾ Thermal pad contour optional with dimensions D1 and E1
- (6) Lead finish uncontrolled in L1
- (7) Ø P to have a maximum draft angle of 1.5° to the top of the part with a maximum hole diameter of 3.91 mm
- (8) Dimension b2 and b4 does not include dambar protrusion. Allowable dambar protrusion shall be 0.1 mm total in excess of b2 and b4 dimension at maximum material condition



VERSION 2: FACILITY CODE = Y



	MILLIN	IETERS	
DIM.	MIN.	MAX.	NOTES
A	4.58	5.31	
A1	2.21	2.59	
A2	1.17	2.49	
b	0.99	1.40	
b1	0.99	1.35	
b2	1.53	2.39	
b3	1.65	2.37	
b4	2.42	3.43	
b5	2.59	3.38	
С	0.38	0.86	
c1	0.38	0.76	
D	19.71	20.82	
D1	13.08	-	

	MILLIN	IETERS	
DIM.	MIN.	MAX.	NOTES
D2	0.51	1.30	
E	15.29	15.87	
E1	13.72	-	
е	5.46	BSC	
Øk	0.2	254	
L	14.20	16.25	
L1	3.71	4.29	
ØР	3.51	3.66	
Ø P1	-	7.39	
Q	5.31	5.69	
R	4.52	5.49	
S	5.51	BSC	

Notes

- ⁽¹⁾ Dimensioning and tolerancing per ASME Y14.5M-1994
- ⁽²⁾ Contour of slot optional
- (3) Dimension D and E do not include mold flash. Mold flash shall not exceed 0.127 mm (0.005") per side. These dimensions are measured at the outermost extremes of the plastic body
- ⁽⁴⁾ Thermal pad contour optional with dimensions D1 and E1
- ⁽⁵⁾ Lead finish uncontrolled in L1
- ⁽⁶⁾ Ø P to have a maximum draft angle of 1.5 to the top of the part with a maximum hole diameter of 3.91 mm (0.154")
- ⁽⁷⁾ Outline conforms to JEDEC outline TO-247 with exception of dimension c

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VERSION 3: FACILITY CODE = N



	MILLIMETERS			MILLIMETERS	
DIM.	MIN.	MAX.	DIM.	MIN.	MAX
А	4.65	5.31	D2	0.51	1.35
A1	2.21	2.59	E	15.29	15.87
A2	1.17	1.37	E1	13.46	-
b	0.99	1.40	e	5.46	BSC
b1	0.99	1.35	k	0.:	254
b2	1.65	2.39	L	14.20	16.10
b3	1.65	2.34	L1	3.71	4.29
b4	2.59	3.43	N	7.62	BSC
b5	2.59	3.38	Р	3.56	3.66
С	0.38	0.89	P1	-	7.39
c1	0.38	0.84	Q	5.31	5.69
D	19.71	20.70	R	4.52	5.49
D1	13.08	-	S	5.51	BSC

Notes

⁽¹⁾ Dimensioning and tolerancing per ASME Y14.5M-1994

⁽²⁾ Contour of slot optional

(3) Dimension D and E do not include mold flash. Mold flash shall not exceed 0.127 mm (0.005") per side. These dimensions are measured at the outermost extremes of the plastic body

⁽⁴⁾ Thermal pad contour optional with dimensions D1 and E1

⁽⁵⁾ Lead finish uncontrolled in L1

⁽⁶⁾ Ø P to have a maximum draft angle of 1.5 to the top of the part with a maximum hole diameter of 3.91 mm (0.154")



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